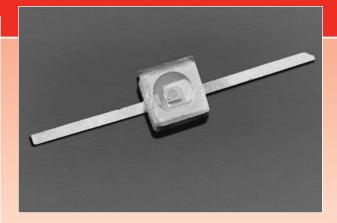
## FCI-InGaAs-XXX-CCER

High Speed InGaAs Photodiodes Mounted on Cavity Ceramic Packages

FCI-InGaAs-XXX-CCER with active area sizes of 70µm, 120µm, 300µm, 400µm and 500µm are part of OSI Optoelectronics's high speed IR sensitive photodiodes mounted on gull wing ceramic substrates with glass windows. These devices have a glass window attached to the ceramic where fibers can be directly epoxy mounted onto. The chips can be epoxy or eutectic mounted onto the ceramic substrate. These devices can be provided with custom AR coated windows.

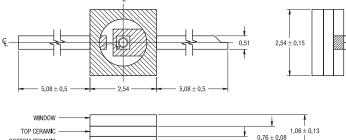


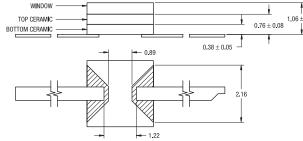
## APPLICATIONS

- High Speed Optical Communications
- Gigabit Ethernet/Fibre Channel
- SONET / SDH, ATM
- Diode Laser Monitoring
- Instrumentation

## FEATURES

- Low Noise
- High Responsivity
- High Speed
- Spectral Range
  900nm to 1700nm





## **Absolute Maximum Ratings** PARAMETERS SYMBOL MIN MAX UNITS °C Storage Temperature T<sub>stg</sub> -40 +85 Operating Temperature 0 +70 °C T<sub>op</sub> Soldering Temperature T<sub>sld</sub> ---+260 °C

• All units in millimeters.

Notes:

• All devices are mounted with low out gassing conductive epoxy with tolerance of ±25µm. Eutectic mounting is also available upon request.

Electro-Op		naracteristi																23°C
PARAMETERS	SYMBOL	CONDITIONS	FCI-InGaAs-70CCER MIN TYP MAX			FCI-InGaAs-120CCER MIN TYP MAX			FCI-InGaAs-300CCER MIN TYP MAX			FCI-InGaAs-400CCER			FCI-InGaAs-500CCER			UNITS
Active Area Diameter	AA <sub>o</sub>			70			120			300			400			500		μm
Responsivity	R <sub>λ</sub>	λ=1310nm	0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		A/W
		λ=1550nm	0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		
Capacitance	Cj	V <sub>R</sub> = 5.0V		0.65			1.0			10.0			14.0			20.0		pF
Dark Current	I <sub>d</sub>	V <sub>R</sub> = 5.0V		0.03	2		0.05	2		0.30	5		0.40	5		0.50	20	nA
Rise Time/ Fall Time	t <sub>r</sub> /t <sub>f</sub>	$V_{R} = 5.0V,$ $R_{L} = 50\Omega$ 10% to 90%			0.20			0.30			1.5			3.0			10.0	ns
Max. Revervse Voltage					20			20			15			15			15	v
Max. Reverse Current					1			2			2			2			2	mA
Max. Forward Current					5			5			8			8			8	mA
NEP				3.44E- 15			4.50E- 15			6.28E- 15			7.69E- 15			8.42E- 15		W/√Hz